Durafuse[™]LT

An Industry Leader in Low Temperature solder

Low Temperature Solder

Industry Drivers

- Reduce cost in component, substrate, and soldering temperature
- Heat sensitivity of some components and flex polymers
- Reduce Thermal Warpage
	- o Component miniaturization (Intel driven)
	- Multilayer board warpage (Server applications)
- Eliminate Wave Soldering Process
- Step Soldering
	- o RF Shield Attachment
	- o Rework Applications
	- o Avoid Solder Squeezeout

Warpage as a Function of Temperature

Figure 4: Warpage as a function of temperature during simulated reflow.

Thermal warpage is impacted by increasing component complexity, decreasing ball pitch, substrate material, size, and package thickness

HIP/HOP Solder to Pad Separation

Although highly component specific, a temperature change to 200°C can result in a dramatic warpage reduction

Low Temp 3 Prong Support

The next level of Drop Test reliability with our novel low temperature mixed alloy system

Doped bismuth alloy bringing increased TCT reliability and security to your low temperature process

Bismuth and indium solutions backed by decades of experience, ideal for traditional applications

Durafuse[™] LT **Advantages:**

Melting temperature >180˚C

Reflow below 210˚C

Good mechanical shear strength up to 150~165˚C

Good thermal & electrical conductivity

Design of Durafuse™LT Patent Pending

Low Temperature Drop Shock Solution

Durafuse™ LT for drop shock contains an low melting indium based alloy which initiates joint fusion, while the high melting SAC alloy provides enhanced strength and durability

Unique Melt Characteristics

High indium (≥20%) content alloy low melting peak (DSC)

Reflowed Durafuse™ LT contains a low percentage of indium, avoiding formation of low melting In-Sn or InSn₄-In eutectic

Post Reflow Melt Characteristics

DSC: Melt, Remelt

Post Reflow Solidus 188 ℃ Second DSC Solidus 191 ℃ Post Reflow Liquidus 206 ℃

Roughened surface demonstrates mixed crystal formation with partially diffused Sn

During reflow Durafuse™ LT introduces more Sn into the liquid phase to increase joint melting temperature and eliminate the low melting peak typically found with In/Sn solders

Joint Microstructure

Despite Sn-rich colonies causing crystal structure variation and roughened solder joint appearance, SEM analysis shows no distinct interfaces between compositions

After reflow the "darker" Sn-rich colonies are embedded in InSn matrix

Ω 50 100 150 200 250 0.0 1.0 2.0 3.0 4.0 5.0 **Temperature (** Temperature (°C) **Time (Min) Durafuse™ LT Example Reflow Profiles LT alloy Liquidus < 190 SAC alloy Liquidus ≥ 220 RAMP SOAK COOLING** *A plateau region between low and high-temperature alloy liquidus temperatures facilitates alloy integration. Peak reflow temperatures from 200-210*°*C*

Durafuse™ LT is designed for use with Indium 5.7LT-1. The flux has a high thermal tolerance and is compatible with a linear ramp rate of 0.5-2°C/s

Drop Shock Methodology

Indium Corporation uses a ball drop - type test to determine drop shock reliability

Drop Test BGA

10x10 grid Diameter 0.6MM Pitch 4.5MM

Drop Shock Testing

Durafuse™ LT (200°**C peak reflow) drop shock resistance is over two orders of magnitude higher than Bi-Sn (170**°**C peak reflow)**

Durafuse (210C) Drop Shock vs SAC305 Weibull plot of failure from 110g ball with 500mm drop height 99 **SAC305** 90 80 **P245˚C 4mil** 70 60 50 40 **Durafuse™** 30 Percent **P210˚C** 20 110am steel ball 500mm drop height Paste: Ball ratio ≈ 0.5 500 750 1000 1250 1500 1750 2000 **Drop Number**

Durafuse™ LT (210℃ reflow) drop shock **surpassed SAC305**

Reflow Profile Optimization

Peak Temp: 200˚C Time @ Peak: 120 seconds

Peak Temp: 205˚C Time @ Peak: 100 seconds

Peak Temp: 210˚C Time @ Peak: 60-70 seconds

Fusion Time vs Drop-shock

Reflow oven belt rate Fast Medium Slow

Drop Shock Failure Mode

SAC305

Durafuse™ LT P200 Durafuse™ LT P210

Ruptures within the IMC interface

Solder failure close to PCB side. Grainy surface is exposed. Exposed particles are smooth

Fails between solder and IMC. $\rm Cu_6$ Sn $_5$ IMC is exposed. Similar to SAC305.

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Durafuse™ LT Drop Shock "Homogeneous"

only performance. The components used for

testing are the same type and dimension as those in previous tests, but with the solder balls removed to turn the BGA into an LGA.

Drop Shock

Durafuse™ LT Solder Paste Only (LGA)

Durafuse™ LT can provide high drop shock performance in a wide array of applications

Performance remains consistent between applications with and without SAC solder balls

> *10x10 grid Pitch 4.5MM*

HT Bond Shear Strength

^{}Oven belt speed remained unchanged*

Durafuse™ LT

Twice the shear strength of indium based low temperature alloys

Maintains shear strength at temperatures beyond bismuth and indium alloy capability

Bond shear strength can be enhanced by using a peak reflow temperature of 210°C

Thermal Cycling

0603 Chip Resistors -40/+125 ℃ **Shear Strength**

After reflow, SAC is slightly *stronger* than or *comparable* to DF.

After 3000 cycles, the relative strength of SAC and DF is *constant*.

OSP has stronger joint than ENIG after reflow

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Thermal Cycling 0805 Chip Resistors -40/+125 ℃ **Shear Strength**

0.00 1.00 2.00 3.00 4.00 5.00 6.00 7.00 **OSP ENIG OSP ENIG SAC 305 P210-3 Control Durafuse LT Force (kgs) 0805 Chip Resistor** 0 Cycles 1000 Cycles 2000 Cycles 3000 Cycles

TCT -40/+125℃ with 10min dwell times for **3000 cycles**

On *OSP* SAC has greater shear strength than DR and after 3000 cycles retains that margin

DF is *comparable* to than SAC305 for *ENIG*.

OSP has stronger joints than ENIG after reflow

Thermal Cycling

BGA192 -40/+125 ℃ **Electrical Failure**

Test Conditions

- 14x14mm BGA package
- 12x12mm die
- 0.8mm ball pitch
- 0.46mm ball diameter
- 0.38mm NSMD chip pad diameter
- OSP surface finish
- 127um stencil thickness
- 45min cycle 10min dwell

AD

0.164

 -12.0 mm s

BGA TCT Failure Mechanism OSP

TCT Failure Analysis

- Failure mechanisms typical of thermal fatigue
- Corner joints failed first during TCT
- Most joints cracked near solder/pad interface
- Mixed cracking
	- Along solder and $Cu₆Sn₅$ IMC boundary and within solder bulk

Elongated plateau at peak temperature enabled spherical joints for all profiles, demonstrating good joint formation

Thermal Cycling

LGA192 -40/+125 ℃ **Electrical Failure**

LGA192 TCT Reliability Weibull - 95% CI

Variable

631.0 1669 11 0.537

Durafuse P200 S

AD 7 0.581

0.111

0.163

Test Conditions

- 14x14mm LGA package
- 12x12mm die
- 0.8mm pad pitch
- 0.38mm chip pad diameter
- ENIG surface finish
- 127um stencil thickness
- 45min cycle 10min dwell

Wetting & Coalescence

Solder Ball Graping

Excellent wetting graping and solder ball performance on ENIG and OSP surfaces

Mechanical Properties

Bulk Material Behavior Anisotropic Flastic Plastic Strain Rate Dependent Characteristic Geometry Matched Microstructure: Grain Size (~single crystal) Intermetalics

Durafuse™ LT Print Testing

Print testing

Continuous Print Test (20 boards)

Response to Pause

Response to Pause Procedure – 4mil stencil

Continuous Print 20 boards

Wipe Stencil

Pause 1hr

Wipe Stencil

Print 6 boards

Wipe Stencil

Print 6 boards

Print Settings

- Type 4 powder in 5.7LT-1
- Pressure 8.6Kg
- Speed 50mm/s
-

Response To Pause

Component: 0201 Chip Resistors

**High transfer efficiency & low variation *Outstanding continuous printing *Excellent response to pause*

Paste RTP vs Aperture Size

Durafuse™ LT retained good response to pause performance after transitioning from 0.635 area ratio to 0.575 area ratio apertures

**Aperture shape: Square *Both solder mask defined and nonsolder mask defined components*

01005 Continuous Print Test

Although Durafuse™ LT T4 powder performed exceptionally well, T5- MC powders are generally recommended for printing 01005s

Cu/Cu assembly

Voiding X-ray prepared using a Cu/Cu assembly and Durafuse™ LT

Rework

Rework is a necessary consideration for many SMT processes

Rework reattachment options

- Durafuse™ LT
	- Dispensable paste
	- Same reflow as printed Durafuse™ LT
- **SAC305**
	- Localized heating avoids damage to sensitive components
- Indalloy®254
	- Available as wire, liquidus 205℃
- Indalloy®227
	- Available as wire, liquidus 187℃

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Flux Reliability

5.7LT-1 was designed for quality performance in low temperature applications

Durafuse™ LT

- **High drop-shock reliability**
	- Reflow profile optimizable
- Proven flux vehicle: Indium5.7LT-1
- T4 and T5-MC powder samples are available

Key Strengths:

Low Temperature reflow

Reduce reflow temperature 40-50°C

High drop shock resilience

- Matches SAC305 capability
- Orders of magnitude superior to bismuth alloys

Shear Strength

• Joint shear strength retained even at elevated temperatures

Step-soldering enhancement

- Solidus above Bi-alloy reflow temperature
- Peak reflow temperature below SAC solidus

Classic Low Temperature Solders

• **Bismuth Based**

Indalloy #281 (58Bi/42Sn) 138˚C Indalloy #282 (57Bi/42Sn/1Ag) 139-140˚C **Indalloy #283 (57.6Sn/42Sn/0.4Ag) 139-144˚C**

• **Indium Based**

Indalloy #1E (52In/48Sn) 118˚C Indalloy #290 (97In/3Ag) 143˚C Indalloy #4 (100In) 157˚C **Indalloy #227 (77.2Sn/20In/2.8Ag) 175-187˚C** Indalloy #254 (86.9Sn/10In/3.1Ag) 204-205˚C

• **Flux Vehicle:**

Current Preferred Option: Indium5.7LT-1:

Offers better solder beading and solder balling performance that Indium5.7LT **Other Options: Indium5.7LT & NC-SMQ80**

Additional Phase Diagrams

Thermal Warpage

Figure 4. Warpage of bottom PoP device is approximately 89 microns (3.5 mils)

Figure 6. Maximum warpage was 100microns well below the allowable limit for a 1mm pitch device. Dr. Anselm SMTAI 2014

"Most components warp suddenly when a T_g of a material is reached, when moisture evolves at 100°C or for any of a host of other reasons"